

Structural Stability & Electronic properties of IV-VI thin Nanowires



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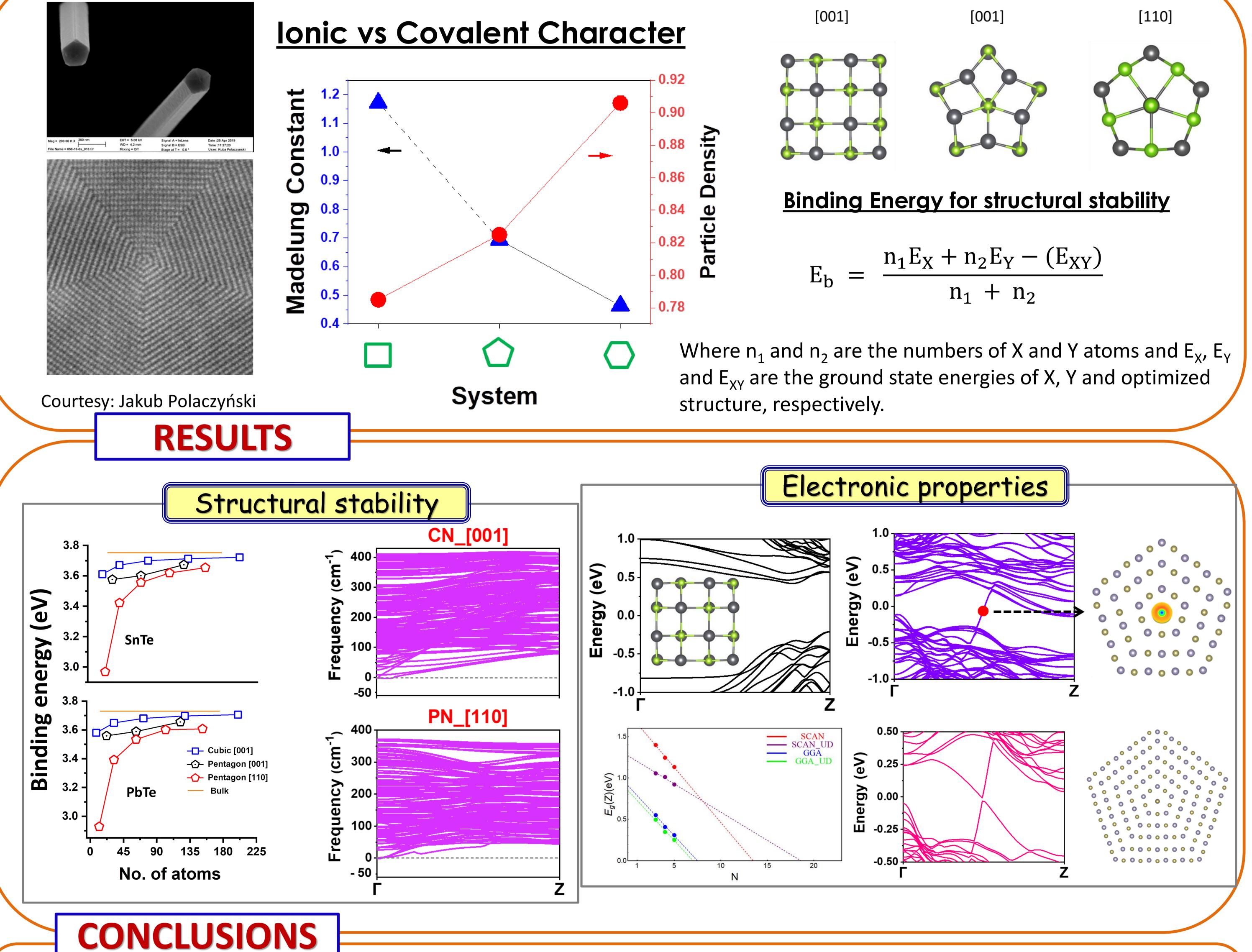
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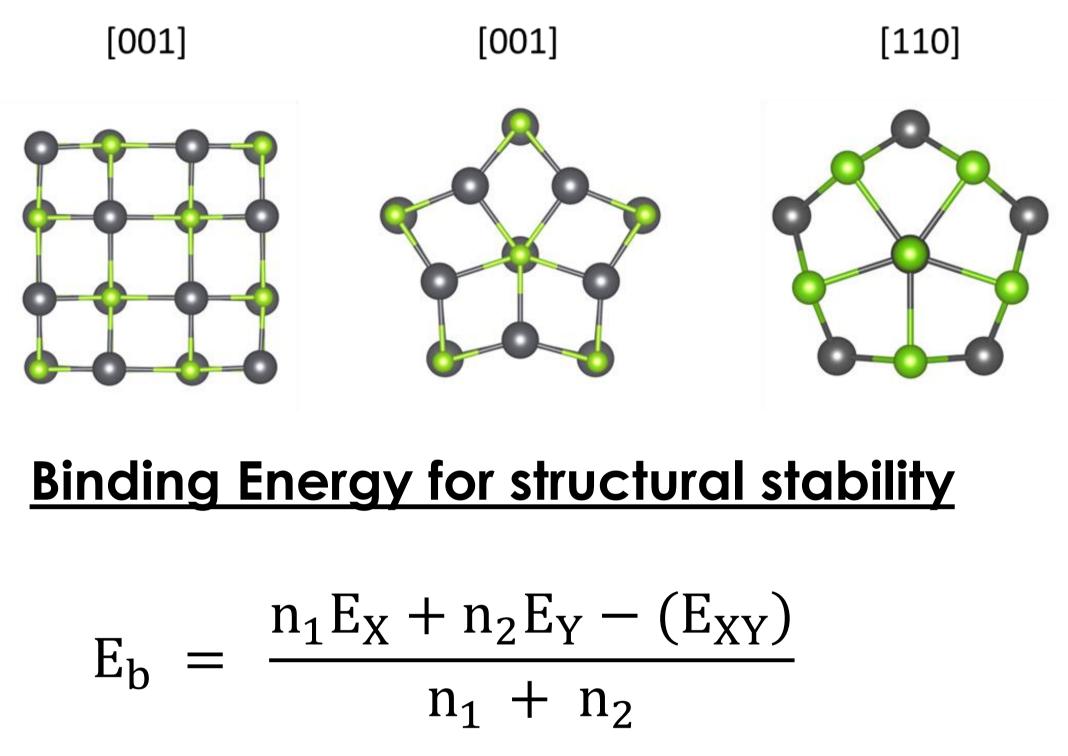
ABSTRACT

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We used density functional theory to study the electronic properties and structural stability of thin SnTe and PbTe cubic nanowires (CNs) and pentagonal nanowires (PNs) grown along [001] and [110] directions. The band structures illustrated a trivial insulating behavior for thin CNs, while the bands connecting valence and conduction electrons are observed for thin PNs within a trivial band structure. We estimated that topological band structure is expected in SnTe CNs for thicknesses larger than 13 nm, and we can assume a similar value for the PNs. The bands connecting valence and conduction electrons in thin PNs mainly originate from the central atom as observed from partial charge density making the disclination responsible for band crossing and thus metallicity. Moreover, the binding energies revealed that the stability increases as the thickness of nanowires increases and CNs are more stable than PNs. In addition, the absence of imaginary phonons modes in the phonon spectra indicate the dynamical stability of CNs and PNs. Therefore, the PNs are in a metastable structural phase.

MOTIVATION & INTRODUCTION





The pentagonal structure bears intermediate values for Madelung constant and particle density implying that if the bond is

